

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200310842-1

APPLICATION NO.

CONFIRMATION NO.

APPLICANT

Peter J. Fricke et al.

FILING DATE

02-04-2004

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	1A	5,811,870-B	09-22-1998	Bhattacharyya et al.	
	1B	5,617,351-B	04-01-1997	Bertin et al.	
	1C	5,481,128-B	01-02-1996	Hong	
	1D	5,468,663-B	11-21-1995	Bertin et al.	
	1E	5,451,535-B	09-19-1995	Chan et al.	
	1F	5,331,189-B	07-19-1994	Chan et al.	
	1G	5,298,447-B	03-29-1994	Hong	
	1H	4,752,812-B	06-21-1988	Arienzo et al.	
	1I	4,688,078-B	03-18-1987	Hseih	
	1J	4,471,471-B	09-11-19	DiMaria	
	1K	4,446,535-B	05-01-1984	Gaffney et al.	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L					
	1M					
	1N					
	1O					
	1P					

- OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	H. CHAO "Electrically alterable read-only memory array" IBM Tech. Discl. Bull., June 1982, pp. 41-43
	1R	DIMARIA et al., "Electrically-Alterable Memory Using A Dual Electron Injector Structure," Electron Dev. Let., EDL-1 (9), Sept. 1980, pp. 179-181
	1S	DIMARIA et al. "Two carrier dual injector structur , " IBM Tech. Discl. Bull., Aug 1980, pp. 1277-1279

EXAMINER

DATE CONSIDERED

PATENT APPLICATION

Sheet 1 of 3

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200310842-1	APPLICATION NO.	CONFIRMATION NO.
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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	1A	20030189851A	10-09-2003	Brandenberger et al.	
	1B	20030185048A	10-02-2003	Fricke et al.	
	1C	20030178693A	09-25-2003	Bhattacharyya et al.	
	1D	20030161175A	08-28-2003	Fricke et al.	
	1E	20030151948A	08-14-2003	Bhattacharyya	
	1F	20030081446A	05-01-2003	Fricke et al.	
	1G	20030072126A	04-17-2003	Bhattacharyya	
	1H	6,549,447-B	04-15-2003	Fricke et al.	
	1I	20030042534A	03-06-2003	Bhattacharyya	
	1J	20020028541A	03-07-2002	Lee et al.	
	1K	6,344,373-B	02-05-2002	Bhattacharyya et al.	

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	1L					
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	1Q	DIMARIA et al., "Enhanced conduction and minimized charge trapping in electrically alterable read-only memories using off-stoichiometric silicon dioxide films" J. Appl. Phys. 55 (8), 15 Apr 1984, pp. 3000-3019
	1R	DIMARIA et al., "Enhanced storage dynamic cell using composite silicon-rich SiO ₂ and thermal SiO ₂ layers" IBM Tech. Discl. Bull., Mar. 1984, pp. 5380-5383
	1S	DIMARIA et al., "Use of composite silicon-rich SiO ₂ / and SiO ₂ / layers or off-stoichiometric CVD SiO ₂ / layers for improvement of poly 1 to poly 2 dielectric" IBM Tech. Discl. Bull., May 1983, p. 6417

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	1A	4,432,072-B	02-14-1984	Chao et al.	
	1B	4,363,110-B	12-07-1982	Kalter et al.	
	1C				
	1D				
	1E				
	1F				
	1G				
	1H				
	1I				
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	1Q	DIMARIA et al. "Dual electron injector structure" Appl. Phys. Lett. 37(1), 1 Jul. 1980, pp. 61-64
	1R	DIMARIA et al. "High current injection into SiO ₂ from Si rich SiO ₂ films and experimental applications," J. Appl. Phys., 51(5), May 1980, pp. 2722-2735
	1S	DIMARIA et al., "High current injection into SiO ₂ using Si-rich SiO ₂ films and experimental applications," in "The Physics of MOS Insulators" (G. Lucovsky et al., Eds.) Pergamon Press, New York, 1980

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